NSN 5962-01-352-7912

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View Online at https://aerobasegroup.com/nsn/5962-01-352-7912
Overall Length:
0.540 inches
Overall Height:
Between 0.045 inches and 0.100 inches
Overall Width:
Between 0.745 inches and 1.040 inches
Body Length:
0.540 inches
Body Width:
Between 0.245 inches and 0.300 inches
Body Height:
Between 0.045 inches and 0.100 inches
Maximum Power Dissipation Rating:
303.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Bipolar and high impedance and w/clock and w/enable and monolithic
Inclosure Material:
Ceramic
Inclosure Configuration:
Flat pack
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
12 input
Case Outline Source And Designator:
F-9 mil-m-38510
Current Rating Per Characteristic:
55.00 milliamperes reverse current, dc absolute
Terminal Surface Treatment:
Solder
Product Name:
Combinatorial and-or-invert gate array
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 7.0 volts power source
Time Rating Per Chacteristic:
50.00 nanoseconds propagation delay time, high to low level output and 50.00 nanoseconds propagation delay time, low to high level
output
Memory Device Type:

Pal

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Fiig: A458a0



Special Features:
Nuclear hardness critical items
Nuclear Hardness Critical Feature:
Hardened
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.
Terminal Type And Quantity:
20 flat leads
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
Yes - demil/mli